Lee, et al. Applicants: Application No. Not yet assigned Filed: March 9, 2004 Buried Bit Line Non-Volatile Floating Gate Memory Cell With Independent Controllable **INFORMATION DISCLOSURE STATEMENT** Control Gate In A Trench, And Array Thereof, And Method Of For: Formation Group Art Unit: Not yet assigned Examiner: Not yet assigned Attorney Docket No.: 2102397-992471

Commissioner of Patents and Trademarks P.O. Box 1450					
Alexandria, VA 22313-1450					
Dear Sir:					
hereby make	e of r	ance with the provisions of 37 C.F.R. § 1.56(a) and 37 C.F.R. § 1.97, Applicant(s) ecord the references listed on the accompanying Form PTO-1449 for consideration by connection with the examination of the above-identified patent application.			
This	Infor	rmation Disclosure Statement:			
(a)		accompanies a new patent application submitted herewith.			
(b)		is filed within three (3) months of the Filing Date or before the mailing date of a First Office Action on the merits; OR			
(c)		after the period defined in (b) but before the mailing date of a Final Rejection or Notice of Allowance, OR			
(d)		is filed after the first Office Action and more than three months after the application's filing date or PCT national stage date of entry filing but, as far as is known to the undersigned prior to the mailing date of either a final rejection or a notice of allowance, and is accompanied by either the fee (\$180) set forth in 37 CFR § 1.17(p) or a certification as specified in 37 CFR § 1.97(e), as checked below OR			
(e)		is filed after the mailing date of either a final rejection or a notice of allowance, and the issue fee has not been paid, and is accompanied by the requisite petition fee (\$130) set forth in 37 CFR § 1.17(I)(1) and a certification as specified in 37 CFR § 1.97(e), as checked below. This document is to be considered as a petition requesting consideration of the information disclosure statement.			
As required under § 1.97(e), Applicants, through the undersigned, hereby state either that [check the appropriate space]:					
(f)		Each item of information contained in the Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing date of the Information Disclosure Statement; or			
(g)		No item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this Statement after making reasonable inquiry, no item of information contained in the Information Disclosure Statement was known to any individual designated in § 1.56(c) more than three months prior to the filing of the Information Disclosure Statement.			

The Commissioner is authorized to charge any deficiencies and credit any overpayment of fees to our Deposit Account No. O7-1896

Respectfully submitted,

Date: March 9, 2004

GRAY CARY WARE & FREIDENRICH LLP

By: Reg. No. Ronald L. Yin (Reg. No. 27,607)
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2000 University Avenue
East Palo Alto, CA 94303-2248
Tel. No. 650-833-2437

It is respectfully requested that the references shown on the attached Form PTO-1449 be made

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as EXPRESS MAIL (EV 302280244 US) in an envelope addressed to: Commissioner of Patents & Trademarks, P.O. Box 1450, Alexandria, VA 22313-1450, Mail Stop – Patent Application.

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Form PTO-1449	U.S. DEPT. OF COMMERCE Patent and Trademark Office	Atty. Docket No.: 2102397-992471	Serial No.: Not yet assigned
INFORMATIO	N DISCLOSURE CITATION	Applicants: Lee, et al.	
	al sheets if necessary)	Filing Date: March 9, 2004	Group Art Unit: Not yet assigned

U.S. PATENT DOCUMENTS

Examiners Initials	Patent Number	Date	Name	Class	Subclass	Filing Date
	2002/0163031	11-2002	Lee et al			
	A1	<u> </u>				
	2002/0056870	05-2002	Lee et al			
	Al			1		L
	5,021,999	06-1991	Kohda et al			
	5,029,130	07-1991	Yeh			
	6,093,945	07-2000	Yang, Yu-Hao			
	6,103,573	08-2000	Harari et al			
	6,281,545	08-2001	Liang et al			
	6,420,231	07-2002	Harari et al			
	6,426,896	07-2002	Chen			
	6,597,036	07-2003	Lee et al			

Examiner:	Date Considered:			
EXAMINER: Initial if citation considered, whether or not c	itation is in conformance with MPEP '609; Draw line			
through citation if not in conformance and not considered. Include copy of this form with next communication to the				
applicant.				

FOREIGN PATENT DOCUMENTS

Document number	Date	Country	Class	Sub-class	Transla	ation
					YES	NO
·						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

IEEE, 2002, entitled "Quantum-well Memory Device (QW/MD) With Extremely Good
Charge Retention," Z. Krivokapic, et al. (4 pages)

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Examiner:	Date Considered:				
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